

Atty Docket No.
MAT-9
Applicants:
Timans et al
Filing Date
July 28, 2003

Serial No.: 10/629,400

Group 2812

(Use Several Sheets if Necessary)

U.S. Patent Documents

Examiner						Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
94K	A	4,938,815	7/3/1990	McNeilly	1		
1	В	4,579,080	4/1/1986	Martin et al			
	С	5,561,735	10/1/1996	Camm		- - -	
	D	5,971,565	10/26/1999	Zapata et al		1	
	E	5,874,711	2/23/1999	Champetier et al		1-1	
	F	5,960,158	9/28/1999	Gat et al			
	G	5,997,175	12/7/1999	Champetier et al		 	
	H	6,027,244	2/22/2000	Champetier et al			<u> </u>
	I	6,056,434	5/2/2000	Champetier			
	J	6,127,658	10/3/2000	Kohav			
	K	6,303,411	10/16,2001	Camm et al			
W	L	6,534,752	3/18/2003	Camm et al			-
111	M	6,594,446	7/15/2003	Camm et al		+ +	
38	N	US2002/0102098 A1	8/1/2002	Camm et al	- - - - - - - - - - 		

Foreign Patent or Published Foreign Patent Application

Examiner	l	Document	Publication	Country or		Sub-	Trans	ation
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
311	0	WO 03/060447 A1	7/24/2003	Canada	-		+	
0					·······························			_!

Other Documents

	
No.	Author, Title, Date, Place (e.g. Journal) of Publication
P	Knutson et al, Modeling Of Radiation Heat Transfer And Wafer Temperatures In A Complex Three- Dimensional Rapid Thermal Processing Chamber, 8/31/1994, 2 nd International Rapid Thermal Processing Conference, Monterey California
	Burggraaf, Rapid Wafer Heating: Status 1983, 12/1983, Semiconductor International, pp69-74
R	Gelpey et al, Process Control for a Rapid Optical Annealing System, 1986, Mat Res Soc Symp Proc, Vol 52, Materials Research Society
S	Wilson et al, an Overview and Comparison of Rapid Thermal Processing Equipment: A Users Viewpoint, 1986, Mat Res Soc Symp Proc, Vol 52, Materials Research Society
Т	Blake et al, Slip Free Rapid Thermal Processing, 1987, Mat Res Soc Symp Proc, Vol 92, Materials Research Society
Ū	Celler et al, Drift of Arsenic in SiO ₂ in a Lamp Furnace with a Built-in Temperature Gradient, 1987, Mat Res Soc Symp Proc, Vol 92, Materials Research Society
V	Lord, Thermal and Stress Analysis of Semiconductor Wafers in a Rapid Thermal Processing Oven, August 1988, IEEE Trnasactions on Semiconductor Manufacturing, Vol. 1, No. 3, pp.103-114
W	Hill et al, Reduced Thermal Processing for ULSI, 1989, Plenum Press, pp. 143-180
Х	Rakoschke, Is There a Way to a Perfect Rapid Thermal Processing System?, 1991, Mat Res Soc Symp Proc, Vol 224, Materials Research Society, pp 159-170
Y	Kakoschke, Simulation of Temperature Effects During Rapid Thermal Processing,, 1989, Mat Res Soc Symp Proc, Vol 146, Materials Research Society, pp 473-483
Z	Vandenabeele et al, Impact of Patterned Layers on Temperature Non-uniformity During Rapid Thermal Processing for VSLI-Application, 1989, Mat Res Soc Symp Proc, Vol 146, Materials Research Society, pp 149-160
	P Q R S T U V W X

JAN 0 5 2004 25

0//	AA	Nulmade t al, Pyrometric Emissivity Measurements and Compensation in an RTP Chamber, 1989, Mat
54	Y ar	Research Society, pp 461-466
1	BB	Dilhac et al, Adaptive Process Control for a Rapid Thermal Processor, 1990, SPIE, Vol 1393, Rapid
		Thermal and Related Processing Techniques, pp 395-403
	CC	Dilhac et al, Thermal Model for Rapid Thermal Processors: Theory and Applications, 9/8/1993, 1st
		International Rapid Thermal Processing Conference, Scottsdale, Arizona
	DD	Wei et al, Transient Processing of Titanium Silicides in a Non-Isothermal Reactor, 1985, Mat Res Soc
		Symp Proc, Vol 35, Materials Research Society, pp 465-470
	EE	Pettibone et al, The Effect of Thin Dielectric Films on the Accuracy of Pyrometric Temperature
	<u> </u>	Measurements, 1986, Mat Res Soc Symp Proc, Vol 52, Materials Research Society, pp 210-216
	FF	Dilhac et al, Thermal Modeling of a Wafer in a Rapid Thermal Processor, 11/1995, IEEE
W/-	<u> </u>	Transactions on Semiconductor Manufacturing, Vol 8, No 4, pp 432-439
UAL	GG	Henda et al, Investigation of the Thermal Behavior of a RTP Furnace, 8/1995, IEEE Transactions on
30/		Semiconductor, Manufacturing, Vol 8, No 3, pp 362-365
Examiner 1		Date Considered
Sha	ioni	4 rue turina 5/20/25

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)

Atty Docket No.

MAT-9

Information Disclosure

Applicants:

Statement By Applicant

Timans et al

Filing Date

Group

July 28, 2003

3742

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- clasş	Filing Date
30		5,219,786	6/15/1993	Noguchi		T	
9 - 57		5,561,735	10/1/1996	Camm			
360		5,960,158	9/28/1999	Gat et al			<u> </u>
						<u> </u>	

Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Translat	tion
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
L				Canada				

Other Documents

Examiner				
Initial	No.	Author, Title, Date, Place (e.g.	. Journal) of Publication	
Examiner		0	Date Considered	,
L Sh	ausi	tina Jugua	5/20/05	

Examiner: Initial citation considered. Daw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)

Atty Docket No.

MAT-9

Information Disclosure
Statement By Applicant

Timans et al
Filing Date
Group

July 28, 2003

Group

July 28, 2003

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
95		6,067,931	5/30/2000	Ghezzo et al			
		•					

Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Transla	tion
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
				Canada	1			

Other Documents

Examiner		
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
		_
Examiner	7	Date Considered
\$	May	suting Figure 5/20/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)

Atty-Docket No.
MAT-9

Information Disclosure
Statement By Applicant

Filing Date

C (Use Several Sheets if Necessary)

Atty-Docket No.
Serial No.:
10/629,400

Group

July 28, 2003

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
34		US2001/0047990	12/6/2001	Yoo	<u> </u>		
		US2004/0065657	4/8/2004	Adams et al			
34		US2004/0079746	4/29/2004	Jennings et al			
- 0							

Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Translation	
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
				Canada				

Other Documents

Examiner		1					
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication					
	l						
Examiner ,			J	Date Considered			· <u></u>
Sh	aux	tina =	Jugua		5/20/2	5	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.